

### **INCHANGE SEMICONDUCTOR**

## isc N-Channel MOSFET Transistor

## 2SK683

#### DESCRIPTION

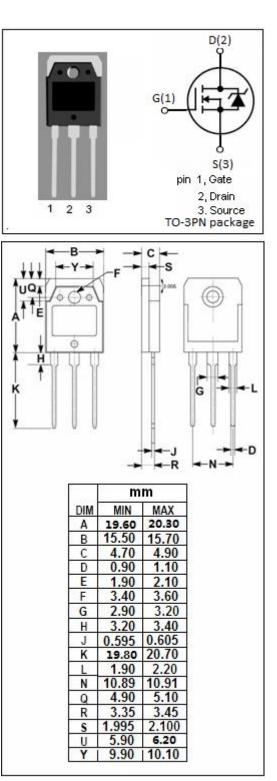
- Drain Current –I\_D=12A@ T\_C=25 $^\circ\!\!\mathrm{C}$
- Drain Source Voltage-: V<sub>DSS</sub>=500V(Min)
- · Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

- low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- · Suitable for switchingregulator, DC-DC convertor

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | ARAMETER                                  | VALUE   | UNIT |
|------------------|---|---------|------|
| V <sub>DSS</sub> | Drain-Source Voltage (V <sub>GS</sub> =0) | 500     | V    |
| V <sub>GS</sub>  | Gate-Source Voltage                       | ±20     | V    |
| ID               | Drain Current-continuous@ TC=25℃          | 12      | А    |
| P <sub>tot</sub> | Total Dissipation@TC=25°C                 | 100     | W    |
| Tj               | Max. Operating Junction Temperature       | 150     | °C   |
| T <sub>stg</sub> | Storage Temperature Range                 | -55~150 | °C   |



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| SYMBOL          | PARAMETER                        | CONDITIONS                                  | MIN | TYP. | МАХ  | UNIT |  |  |  |
|-----------------|----------------------------------|---|-----|------|------|------|--|--|--|
| V(BR)DSS        | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0; I <sub>D</sub> = 10mA   | 500 |      |      | V    |  |  |  |
| $V_{GS(TH)}$    | Gate Threshold Voltage           | V <sub>DS</sub> = 10V; I <sub>D</sub> = 1mA | 2.0 |      | 4.0  | V    |  |  |  |
| Rds(on)         | Drain-Source On-stage Resistance | V <sub>GS</sub> = 10V; I <sub>D</sub> =6A   |     | 0.45 | 0.60 | Ω    |  |  |  |
| $V_{\text{SD}}$ | Diode Forward Voltage            | I <sub>F</sub> = 12A; V <sub>GS</sub> =0    |     | 1.0  |      | V    |  |  |  |
| lgss            | Gate Source Leakage Current      | V <sub>GS</sub> = ±16V; V <sub>DS</sub> = 0 |     |      | ±10  | uA   |  |  |  |
| IDSS            | Zero Gate Voltage Drain Current  | V <sub>DS</sub> =400V; V <sub>GS</sub> = 0  |     |      | 250  | uA   |  |  |  |

#### • ELECTRICAL CHARACTERISTICS (Tc=25°C)

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